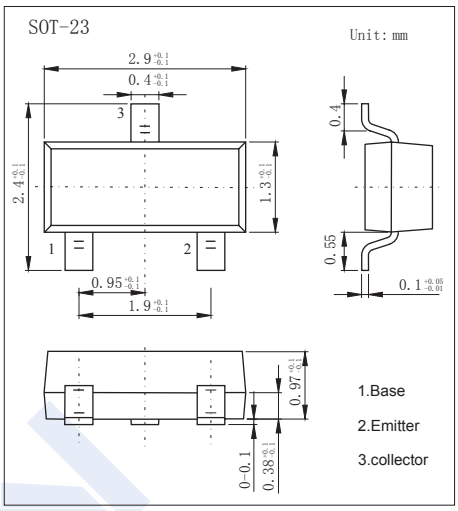
PNP Transistors

FMMT722 (KMMT722)



■ Features

- Collector Current Capability I_C=-1.5A
- Collector Emitter Voltage V_{CEO}=-70V

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-70	V
Collector - Emitter Voltage	V_{CEO}	-70	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-1.5	A
Collector Current - Pulse	I_{CP}	-3	
Base Current	I_B	-0.5	
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-70			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, I_B=0	-70			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -60 V , I_E=0			-100	nA
Collector- emittercut-off current	I_{CES}	V_{CE}= -60 V , I_E=0			-100	
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100 mA, I_B=-10mA			-50	mV
		I_C=-500 mA, I_B=-20mA			-200	
		I_C=-1 A, I_B=-100mA			-220	
		I_C=-1.5 A, I_B=-200mA			-260	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-1.5 A, I_B=-200mA			-1.05	V
Base - emitter turn-on voltage	$V_{BE(on)}$	V_{CE}= -5V, I_C= -1.5A			-1	
DC current gain	h_{FE}	V_{CE}= -5V, I_C= -10mA	300			
		V_{CE}= -5V, I_C= -100mA	300			
		V_{CE}= -5V, I_C= -1A	175			
		V_{CE}= -5V, I_C= -1.5A	40			
		V_{CE}= -5V, I_C= -3A		10		
Turn-on time	t_{on}	V_{CC}=-50V, I_C=-0.5A I_{B1}=-I_{B2}=50mA		40		ns
Turn-off time	t_{off}			700		
Collector output capacitance	C_{ob}	V_{CB}= -10V, f=1MHz			20	pF
Transition frequency	f_T	V_{CE}= -10V, I_C= -50mA,f=100MHz	150			MHz

■ Marking

Marking	722

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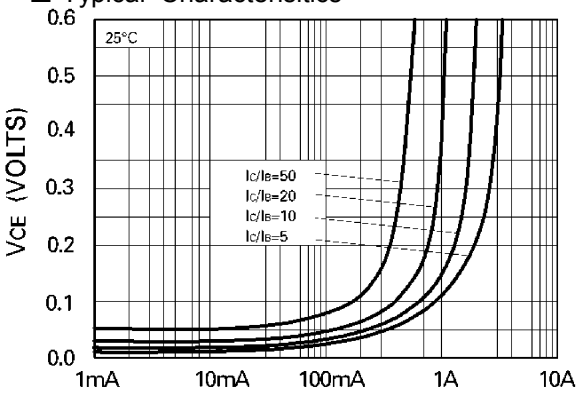
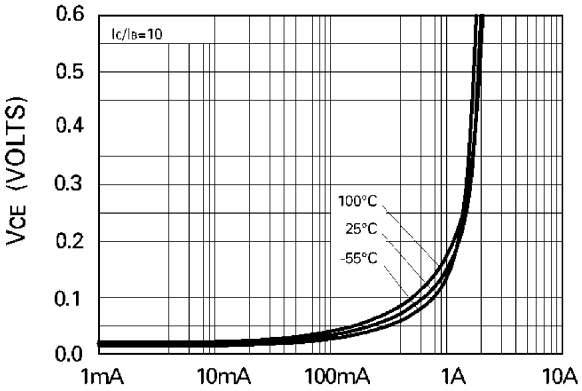
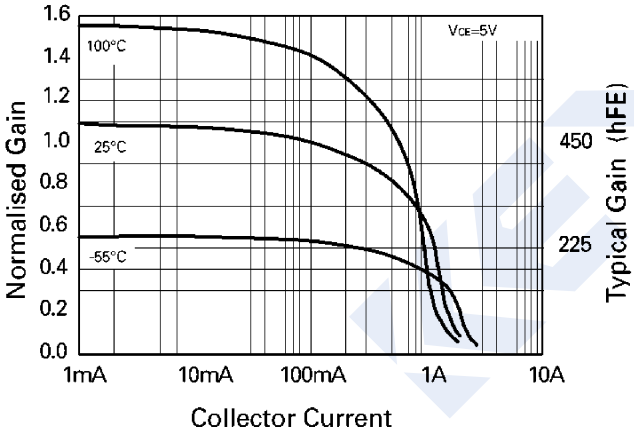
■ Typical Characterisitics



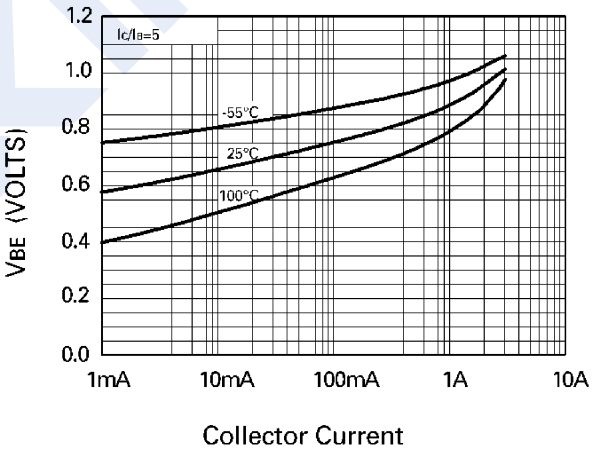
VBE(SAT) vs Ic



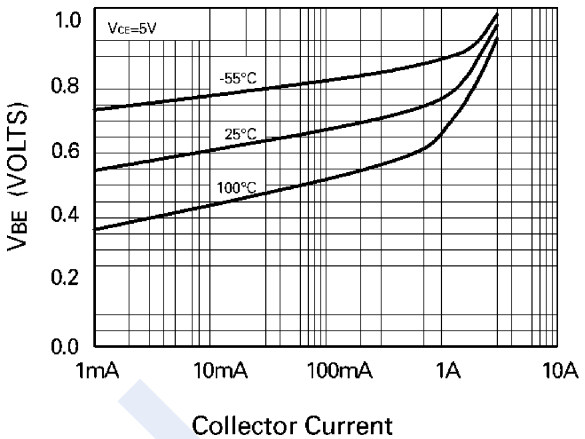
VCE(SAT) vs Ic



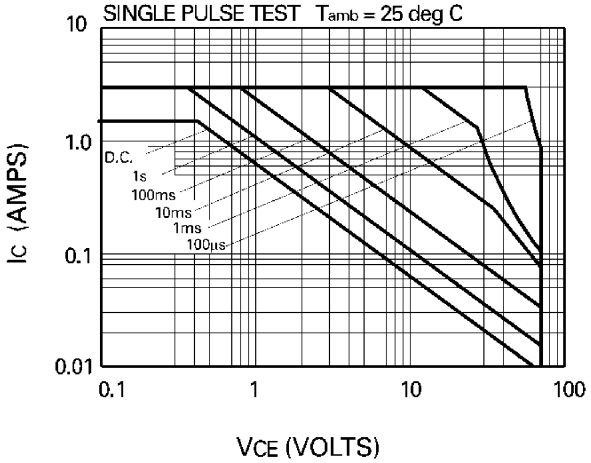
hFE vs Ic



VBE(SAT) vs Ic



VBE(ON) vs Ic



Safe Operating Area

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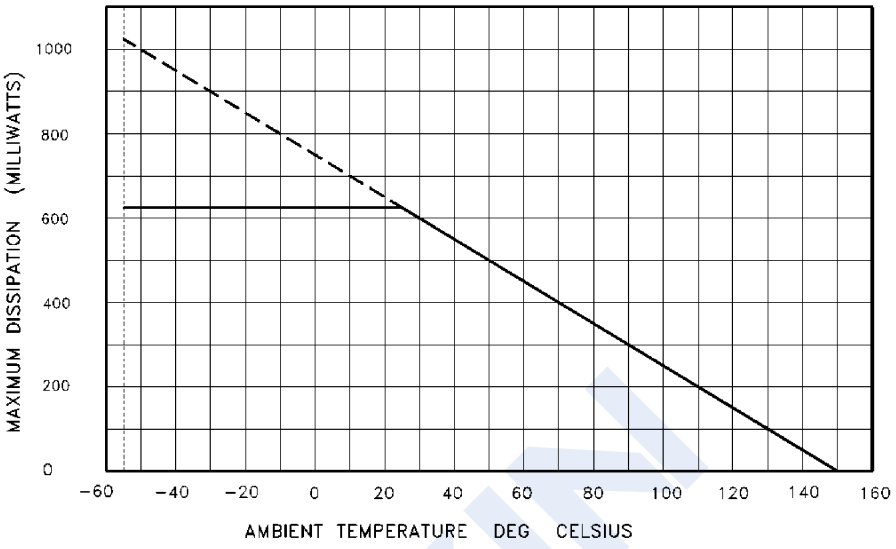
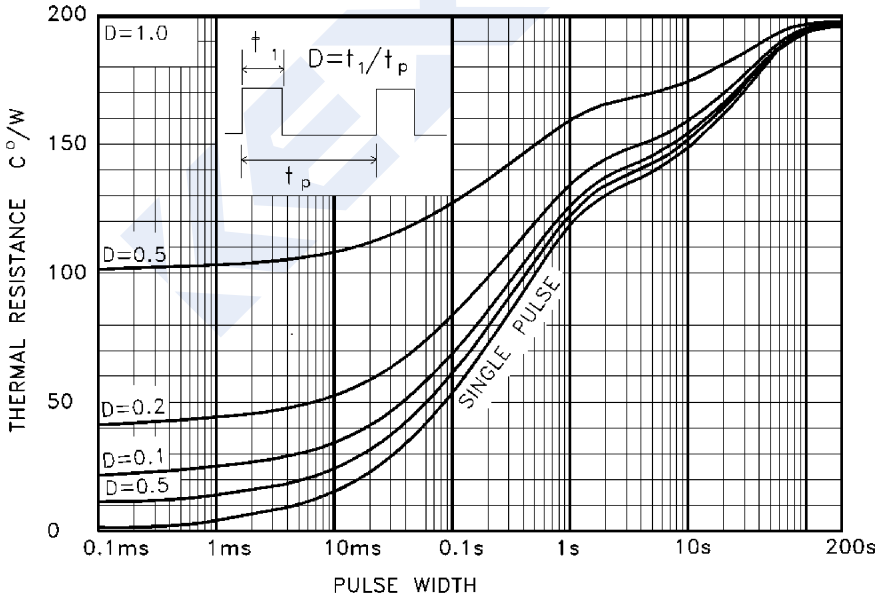
■ Typical Characterisitics



DERATING CURVE



MAXIMUM TRANSIENT THERMAL RESISTANCE